LNA2902L (LN66A(L))

GaAs infrared light emitting diode

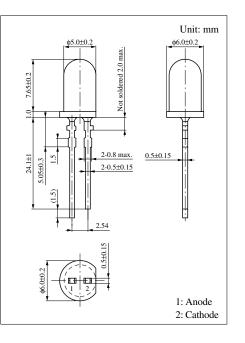
For optical control systems

Features

- High-power output, high-efficiency: $I_e = 9 \text{ mW/sr} (\text{min.})$
- Emitted light spectrum is suited for silicon photodetectors
- Good radiant power output linearity with respect to input current
- Wide directivity: $\theta = 20^{\circ}$ (typ.)
- Transparent epoxy resin package
- Long lead-wire type

Parameter	Symbol	Rating	Unit				
Power dissipation	P _D	160	mW				
Forward current (DC)	I _F	100	mA				
Pulse forward current *	I _{FP}	1.5	А				
Reverse voltage (DC)	V _R	3	V				
Operating ambient temperature	T _{opr}	-25 to +85	°C				
Storage temperature	T _{stg}	-40 to +100	°C				
Operating ambient temperature	T _{opr}	-25 to +85					

Absolute Maximum Ratings $T_a = 25^{\circ}C$



Note) *: Less than f = 100 Hz, duty cycle = 0.1%

Electro-Optical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

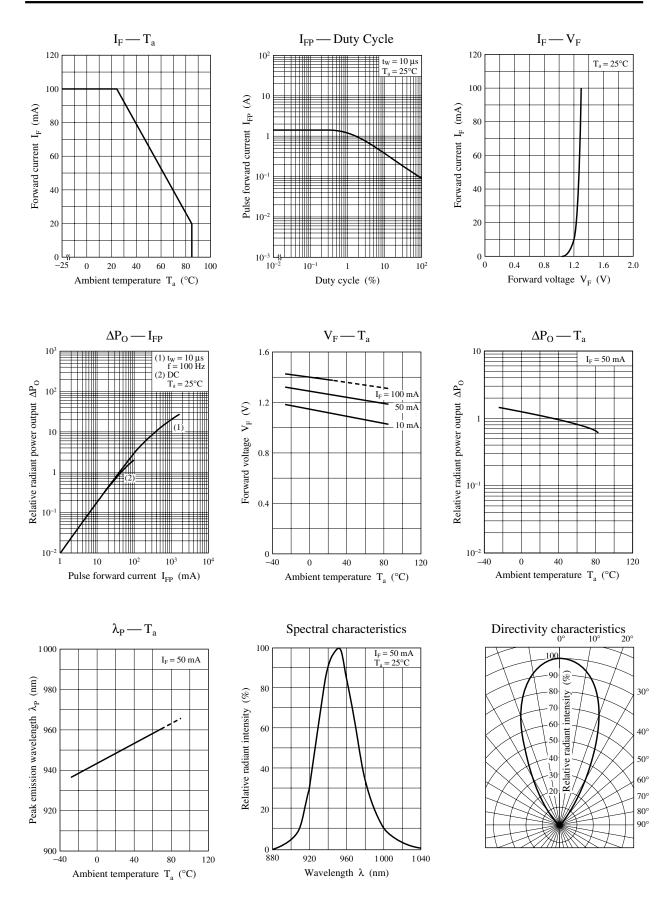
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Radiant intensity	Ie	$I_F = 50 \text{ mA}$	9.0			mW/sr
Total power output	Po	$I_F = 50 \text{ mA}$		12.0		mW
Peak emission wavelength	λ_{P}	$I_F = 50 \text{ mA}$		950		nm
Spectral band width	Δλ	$I_F = 50 \text{ mA}$		50		nm
Forward voltage	V _F	$I_{\rm F} = 100 \ {\rm mA}$		1.4	1.6	V
Pulse forward voltage *1	V _{FP}	$I_{FP} = 1.0 \text{ A}$			3.0	V
Reverse current	I _R	$V_R = 3 V$			10	μΑ
Total capacitance between terminals	Ct	$V_R = 0 V, f = 1 MHz$		35		pF
Beal angle at 50% axial intensity	θ	The angle when the beam intensity is halved.		20		0
Cut-off frequency *2	f_{C}			1		MHz

Note) *1: Less than f = 100 Hz, duty cycle = 0.1%

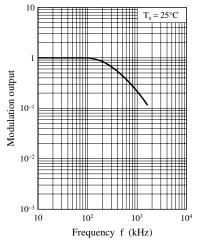
*2: Cut-off frequency
$$f_C: 10 \times \log \frac{P_0 \text{ at } f = f_C}{P_0 \text{ at } f = f_C} = -3$$

$$P_{O}$$
 at f = 50 kHz

Note) The part number in the parenthesis shows conventional part number.



Frequency characteristics



▲ Caution for Safety



Gallium arsenide material (GaAs) is used in this product.

Therefore, do not burn, destroy, cut, crush, or chemically decompose the product, since gallium arsenide material in powder or vapor form is harmful to human health.

Observe the relevant laws and regulations when disposing of the products. Do not mix them with ordinary industrial waste or household refuse when disposing of GaAs-containing products.

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